



Sheet 1 of 1

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 119498	APPLICATION NO. 10/826,354	
INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)		APPLICANT Hiromi OTOMA		EX: Chuc TRAN		
		FILING DATE April 19, 2004		GROUP 2821		
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
CT	1.	JP A 2002-185079 w/abstract & transl.	6/28/2002	JAPAN		
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)						
CT	2.	Kenichi IGA; "Surface Emitting Laser"; IEICE Transactions C-1, Vol. J81-C-1, No. 9; September 1998; pp 483-493				
	3.	H. OTOMA et al.; "Fabrication and Performance of 12 X 12 Matrix-Addressed 780nm Oxide-Confined Vcsel Array"; Bulletin of Solid State Physics and Applications; Vol. 5, No. 1.; 1999; pp 11-15				
CT	4.	Nobuaki UEKI et al.; "Single-Transverse-Mode 3.4-mW Emission of Oxide-confined 780-nm Vcsel's"; IEEE Photonics Technology Letters; Vol. 11, No. 12; December 1999; pp 1539-1541				
	5.	Jun SAKURAI et al.; "10 Gb/s Surface Emission Semiconductor Laser"; Electronic Materials, Vol. 41, No. 11; November 2002; pp 49-52				
CT	6.	M. Grabherr et al.; "Efficient Single-Mode Oxide-Confined GaAs VCSEL's Emitting in the 850-nm Wavelength Regime"; IEEE Photonics Technology Letters; Vol. 9, No. 10, ; October 1997; pp 1304-1306				
	7.	Aaron et al.; "Aperture Placement Effects in Oxide-Defined Vertical-Cavity Surface-Emitting Lasers"; IEEE Photonics Technology Letters; Vol. 10, No. 10; October 1998; pp 1362-1364				
EXAMINER <u>/Chuc Tran/</u>					DATE CONSIDERED <u>05/15/2006</u>	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						

Date: July 29, 2004